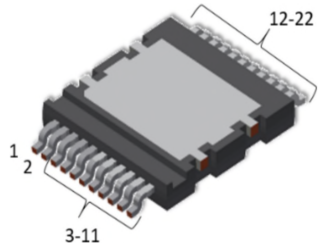
Final datasheet
CoolSiC™ 1200 V SiC MOSFET G2 : Q-DPAK top-side cooling



Halogen-free
Green
Lead-free
RoHS

Features

- V_{DSS} = 1200 V at T_{vj} = 25°C
- I_{DDC} = 22 A at T_C = 100°C
- $R_{DS(on)}$ = 78.1 mΩ at V_{GS} = 18 V, T_{vj} = 25°C
- Very low switching losses
- Overload operation up to T_{vj} = 200°C
- Short circuit withstand time 2 µs
- Benchmark gate threshold voltage, $V_{GS(th)}$ = 4.2 V
- Robust against parasitic turn on, 0 V turn-off gate voltage can be applied
- Robust body diode for hard commutation
- .XT interconnection technology for best-in-class thermal performance
- Suitable Infineon gate drivers can be found under https://www.infineon.com/gdfinder

Potential applications

- Solid-state circuit breaker / Solid-state relay
- EV Charging
- Online UPS / Industrial UPS
- String inverter
- General purpose drives (GPD)
- CAV
- Servo drives

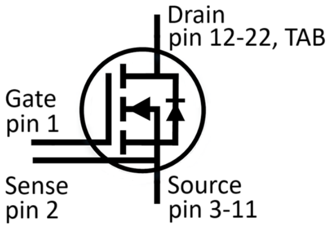
Product validation

- Qualified for industrial applications according to the relevant tests of JEDEC47/20/22

Description

Pin definition:
- Pin 1 - Gate
- Pin 2 - Driver Source contact
- Pin 3…11 - Source
- Piin12-22,Tab - Drain

Note: the source and sense pins are not exchangeable, their exchange might lead to malfunction



Type	Package	Marking
IMCQ120R078M2H	PG-HDSOP-22-U03	12M2H078

Table of contents

1 Package

Table 1 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Storage temperature	T_{stg}		-55		150	°C
Soldering temperature	T_{sold}	reflow soldering (MSL1 according to JEDEC J-STD-020)			260	°C
Thermal resistance, junction-ambient	$R_{th(j-a)}$				62	K/W
MOSFET/body diode thermal resistance, junction-case	$R_{th(j-c)}$			0.65	0.85	K/W

2 MOSFET

Table 2 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Drain-source voltage	V_{DSS}	$T_{vj} \geq 25$ °C		1200	V
Continuous DC drain current for $R_{th(j-c,max)}$, limited by $T_{vj(max)}$	I_{DDC}	$V_{GS} = 18$ V	$T_c = 25$ °C	31	A
			$T_c = 100$ °C	22	
Peak drain current, t_p limited by $T_{vj(max)}$ [1)]	I_{DM}	$V_{GS} = 18$ V		66	A
Gate-source voltage, max. transient voltage [2)]	V_{GS}	$t_p \leq 0.5$ µs, $D < 0.01$		-10...25	V
Gate-source voltage, max. static voltage	V_{GS}			-7...23	V
Avalanche energy, single pulse	E_{AS}	$I_D = 8.9$ A, $V_{DD} = 50$ V, $L = 2.8$ mH		112	mJ
Avalanche energy, repetitive	E_{AR}	$I_D = 8.9$ A, $V_{DD} = 50$ V, $L = 14.1$ µH		0.56	mJ
Short-circuit withstand time	t_{SC}	$V_{DD} \leq 800$ V, $V_{DS,peak} < 1200$ V, $V_{GS(on)} = 15$ V, $T_{vj(start)} = 25$ °C		2	µs
Power dissipation, limited by $T_{vj(max)}$	P_{tot}		$T_c = 25$ °C	176	W
			$T_c = 100$ °C	88	

1) verified by design.
2) **Important note:** The selection of positive and negative gate-source voltages impacts the long-term behavior of the device.The design guidelines described in Application Note AN2018-09 must be considered to ensure sound operation of the device over the planned lifetime.

Table 3 **Recommended values**

Parameter	Symbol	Note or test condition	Values	Unit
Recommended turn-on gate voltage	$V_{GS(on)}$		15...18	V
Recommended turn-off gate voltage	$V_{GS(off)}$		-5...0	V

Table 4 **Characteristic values**

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Drain-source on-state resistance	$R_{DS(on)}$	I_D = 8.9 A	T_{vj} = 25 °C, $V_{GS(on)}$ = 18 V		78.1		mΩ
			T_{vj} = 150 °C, $V_{GS(on)}$ = 18 V		159.2	205	
			T_{vj} = 175 °C, $V_{GS(on)}$ = 18 V		184.8		
			T_{vj} = 25 °C, $V_{GS(on)}$ = 15 V		97.4		
Gate-source threshold voltage	$V_{GS(th)}$	I_D = 2.8 mA, $V_{DS} = V_{GS}$ (tested after 1 ms pulse at V_{GS} = 20 V)	T_{vj} = 25 °C	3.5	4.2	5.1	V
			T_{vj} = 175 °C		3.2		
Zero gate-voltage drain current	I_{DSS}	V_{DS} = 1200 V, V_{GS} = 0 V	T_{vj} = 25 °C			80	µA
			T_{vj} = 175 °C		1.3		
Gate leakage current	I_{GSS}	V_{DS} = 0 V	V_{GS} = 23 V			120	nA
			V_{GS} = -10 V			-120	
Forward transconductance	g_{fs}	I_D = 8.9 A, V_{DS} = 20 V			3		S
Internal gate resistance	$R_{G,int}$	f = 1 MHz, V_{AC} = 25 mV			10		Ω
Input capacitance	C_{iss}	V_{DS} = 800 V, V_{GS} = 0 V, f = 100 kHz, V_{AC} = 25 mV			880		pF
Output capacitance	C_{oss}	V_{DS} = 800 V, V_{GS} = 0 V, f = 100 kHz, V_{AC} = 25 mV			28		pF
Reverse transfer capacitance	C_{rss}	V_{DS} = 800 V, V_{GS} = 0 V, f = 100 kHz, V_{AC} = 25 mV			2.4		pF
C_{oss} stored energy	E_{oss}	V_{DS} = 0...800 V, V_{GS} = 0 V, f = 100 kHz, V_{AC} = 25 mV, Calculated based on C_{oss}			12		µJ
Output charge	Q_{oss}	V_{DS} = 0...800 V, V_{GS} = 0 V, Calculated based on C_{oss}			43.4		nC
Effective output capacitance, energy related	$C_{o(er)}$	V_{DS} = 0...800 V, V_{GS} = 0 V			37.5		pF
Effective output capacitance, time related	$C_{o(tr)}$	I_D = constant, V_{DS} = 0...800 V, V_{GS} = 0 V			54.3		pF

(table continues...)

Table 4 (continued) Characteristic values

Parameter	Symbol	Note or test condition		Values Min.	Values Typ.	Values Max.	Unit
Total gate charge	Q_G	V_{DD} = 800 V, I_D = 8.9 A, V_{GS} = -2/18 V, turn-on pulse			23.2		nC
Plateau gate charge	$Q_{GS(pl)}$	V_{DD} = 800 V, I_D = 8.9 A, V_{GS} = -2/18 V, turn-on pulse			6.1		nC
Gate-to-drain charge	Q_{GD}	V_{DD} = 800 V, I_D = 8.9 A, V_{GS} = -2/18 V, turn-on pulse			4.5		nC
Turn-on delay time	$t_{d(on)}$	V_{DD} = 800 V, I_D = 8.9 A, V_{GS} = 0/18 V, $R_{GS(on)}$ = 2.3 Ω, $R_{GS(off)}$ = 2.3 Ω, $L_σ$ = 15 nH, diode: body diode at V_{GS} = 0 V	T_{vj} = 25 °C		5		ns
			T_{vj} = 175 °C		4.1		
Rise time	t_r	V_{DD} = 800 V, I_D = 8.9 A, V_{GS} = 0/18 V, $R_{GS(on)}$ = 2.3 Ω, $R_{GS(off)}$ = 2.3 Ω, $L_σ$ = 15 nH, diode: body diode at V_{GS} = 0 V	T_{vj} = 25 °C		3.2		ns
			T_{vj} = 175 °C		2.8		
Turn-off delay time	$t_{d(off)}$	V_{DD} = 800 V, I_D = 8.9 A, V_{GS} = 0/18 V, $R_{GS(on)}$ = 2.3 Ω, $R_{GS(off)}$ = 2.3 Ω, $L_σ$ = 15 nH, diode: body diode at V_{GS} = 0 V	T_{vj} = 25 °C		11.7		ns
			T_{vj} = 175 °C		13.6		
Fall time	t_f	V_{DD} = 800 V, I_D = 8.9 A, V_{GS} = 0/18 V, $R_{GS(on)}$ = 2.3 Ω, $R_{GS(off)}$ = 2.3 Ω, $L_σ$ = 15 nH, diode: body diode at V_{GS} = 0 V	T_{vj} = 25 °C		4.8		ns
			T_{vj} = 175 °C		5.6		
Turn-on energy	E_{on}	V_{DD} = 800 V, I_D = 8.9 A, V_{GS} = 0/18 V, $R_{GS(on)}$ = 2.3 Ω, $R_{GS(off)}$ = 2.3 Ω, $L_σ$ = 15 nH, diode: body diode at V_{GS} = 0 V	T_{vj} = 25 °C		75		µJ
			T_{vj} = 175 °C		159		
Turn-off energy	E_{off}	V_{DD} = 800 V, I_D = 8.9 A, V_{GS} = 0/18 V, $R_{GS(on)}$ = 2.3 Ω, $R_{GS(off)}$ = 2.3 Ω, $L_σ$ = 15 nH, diode: body diode at V_{GS} = 0 V	T_{vj} = 25 °C		21		µJ
			T_{vj} = 175 °C		29		

(table continues...)

Table 4 **(continued) Characteristic values**

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Total switching energy[1]	E_{tot}	V_{DD} = 800 V, I_D = 8.9 A, V_{GS} = 0/18 V, $R_{GS(on)}$ = 2.3 Ω, $R_{GS(off)}$ = 2.3 Ω, $L_σ$ = 15 nH, diode: body diode at V_{GS} = 0 V	T_{vj} = 25 °C		102		µJ
			T_{vj} = 175 °C		204		
Virtual junction temperature	T_{vj}			-55		175	°C
Virtual junction temperature	$T_{vj(over)}$	overload, cumulative max. 100 h[2]				200	°C

1) including E_{fr}
2) up to 5000 cycles. Maximum ΔT limited to 100 K.

***Note**: The chip technology was characterized up to 200 kV/µs. The measured dV/dt was limited by measurement test setup and package.*

Characteristics at T_{vj} = 25°C, unless otherwise specified.

3 Body diode (MOSFET)

Table 5 **Maximum rated values**

Parameter	Symbol	Note or test condition	Values	Unit
Drain-source voltage	V_{DSS}	T_{vj} ≥ 25 °C	1200	V
Peak reverse drain current, t_p limited by $T_{vj(max)}$	I_{SM}	V_{GS} = 0 V	66	A

Table 6 **Characteristic values**

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Drain-source reverse voltage	V_{SD}	I_{SD} = 8.9 A, V_{GS} = 0 V	T_{vj} = 25 °C		4.2	5.5	V
			T_{vj} = 100 °C		4.1		
			T_{vj} = 175 °C		4		
MOSFET forward recovery charge	Q_{fr}	V_{DD} = 800 V, I_{SD} = 8.9 A, V_{GS} = 0 V, $-di_{SD}/dt$ = 1000 A/µs, Q_{fr} includes also Q_C	T_{vj} = 25 °C		0.11		µC
			T_{vj} = 175 °C		0.42		
MOSFET peak forward recovery current	I_{frm}	V_{DD} = 800 V, I_{SD} = 8.9 A, V_{GS} = 0 V, $-di_{SD}/dt$ = 1000 A/µs, Q_{fr} includes also Q_C	T_{vj} = 25 °C		7.6		A
			T_{vj} = 175 °C		11.4		

(table continues...)

Table 6 (continued) Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
MOSFET forward recovery energy	E_{fr}	V_{DD} = 800 V, I_{SD} = 8.9 A, V_{GS} = 0 V, $-di_{SD}/dt$ = 1000 A/µs, Q_{fr} includes also Q_C	T_{vj} = 25 °C		6		µJ
			T_{vj} = 175 °C		16		
Virtual junction temperature	T_{vj}			-55		175	°C
Virtual junction temperature	$T_{vj(over)}$	overload, cumulative max. 100 h[1)]				200	°C

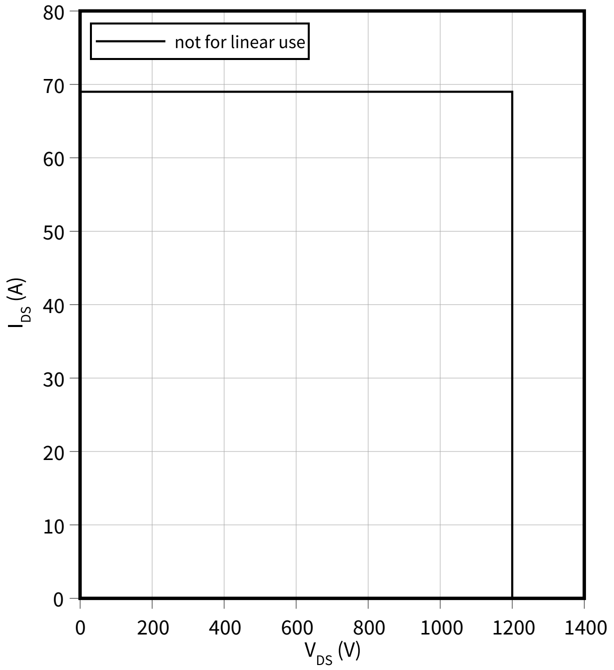
1) up to 5000 cycles. Maximum ΔT limited to 100 K.

4 Characteristics diagrams

Reverse bias safe operating area (RBSOA)

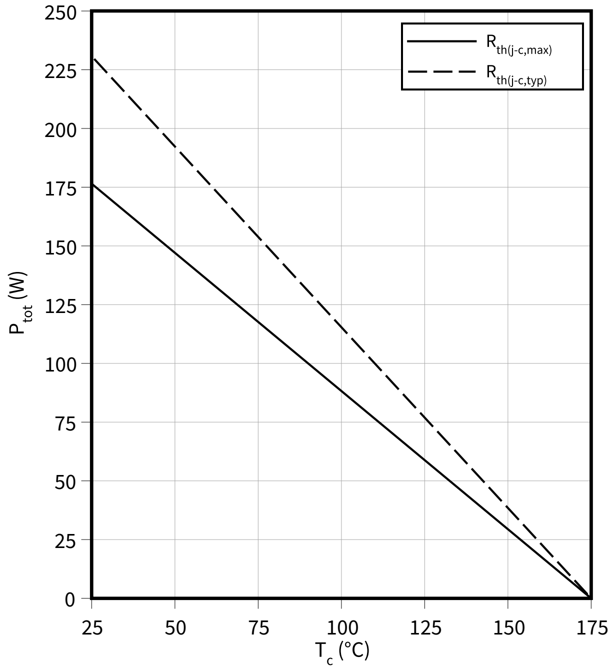
$I_{DS} = f(V_{DS})$

$T_{vj} \leq 200$ °C, $V_{GS} = 0/18$ V, $T_c = 25$ °C



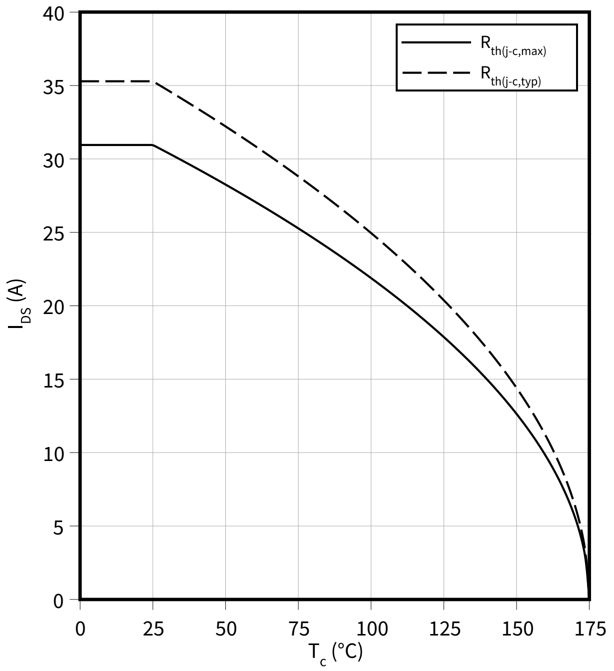
Power dissipation as a function of case temperature

$P_{tot} = f(T_c)$



Maximum DC drain to source current as a function of case temperature limited by bond wire

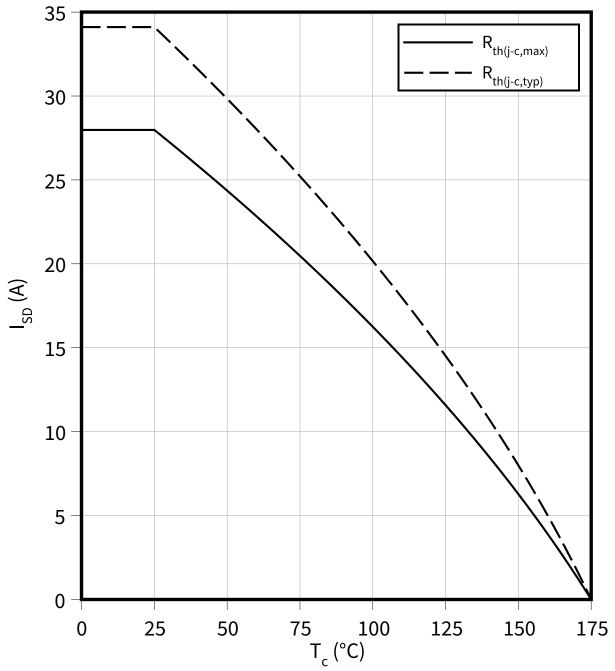
$I_{DS} = f(T_c)$



Maximum source to drain current as a function of case temperature limited by bond wire

$I_{SD} = f(T_c)$

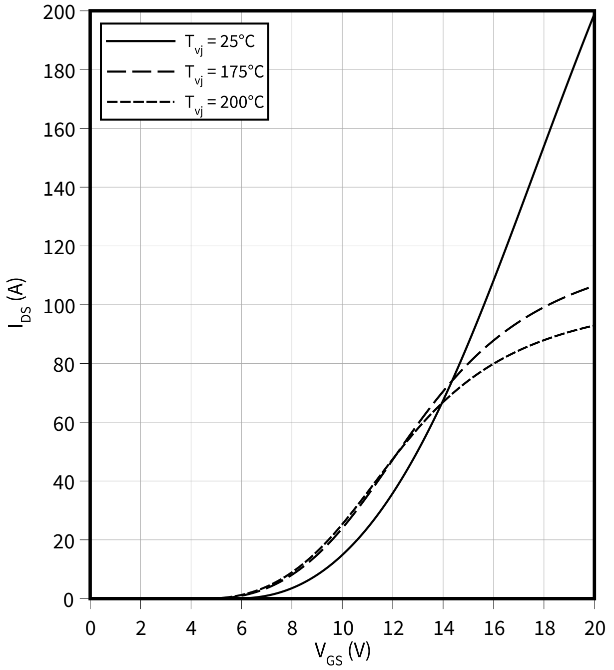
$V_{GS} = 0$ V



Typical transfer characteristic

$I_{DS} = f(V_{GS})$

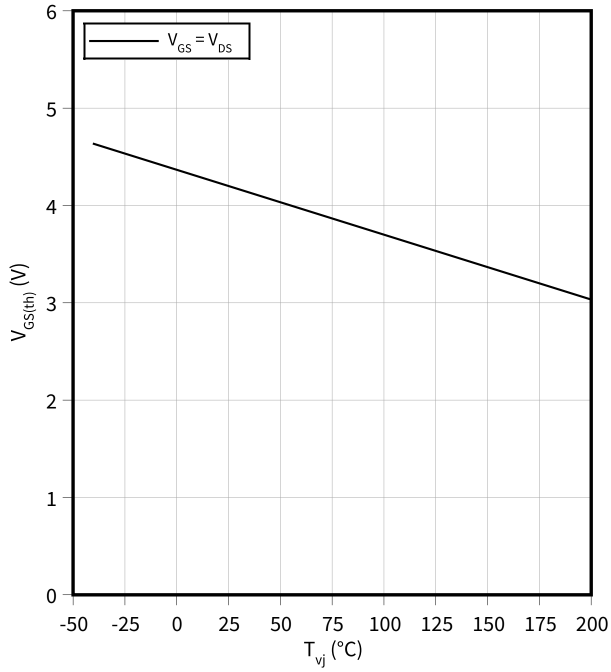
$V_{DS} = 20$ V, $t_p = 20$ µs



Typical gate-source threshold voltage as a function of junction temperature

$V_{GS(th)} = f(T_{vj})$

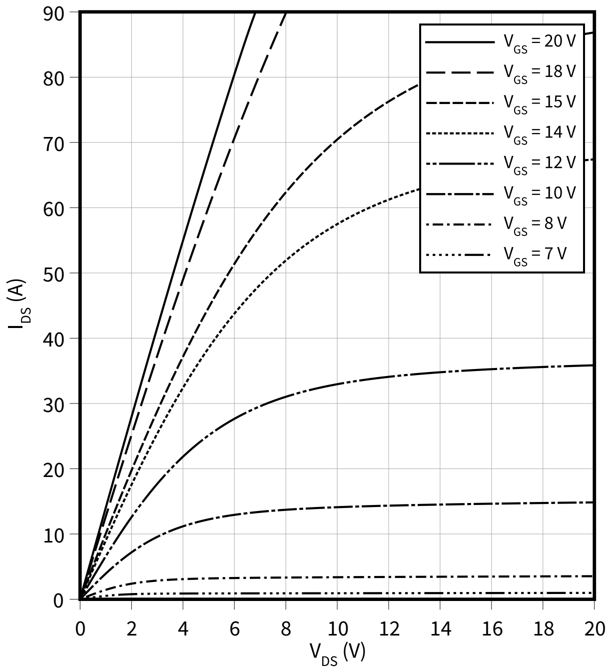
$I_D = 2.8$ mA



Typical output characteristic, V_{GS} as a parameter

$I_{DS} = f(V_{DS})$

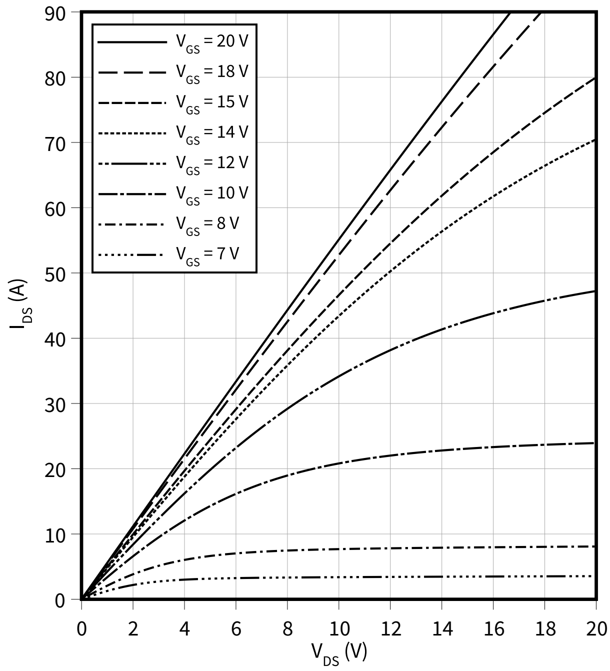
$T_{vj} = 25$ °C, $t_p = 20$ µs



Typical output characteristic, V_{GS} as a parameter

$I_{DS} = f(V_{DS})$

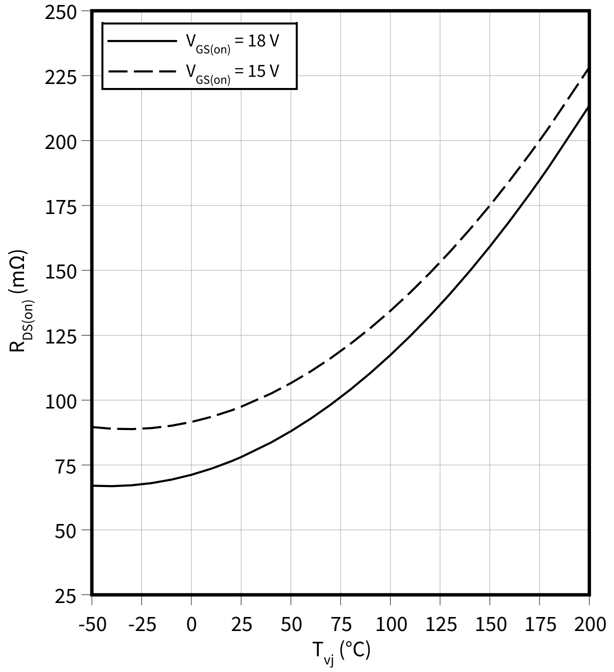
$T_{vj} = 175$ °C, $t_p = 20$ µs



Typical on-state resistance as a function of junction temperature

$R_{DS(on)} = f(T_{vj})$

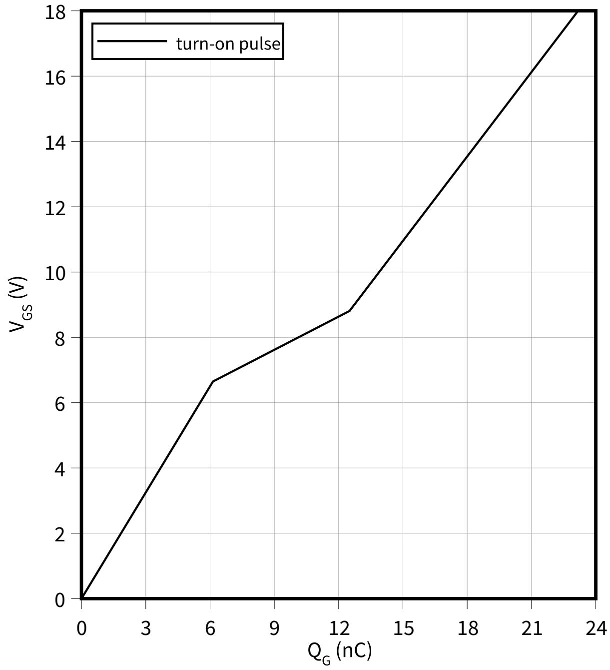
$I_D = 8.9$ A



Typical gate charge

$V_{GS} = f(Q_G)$

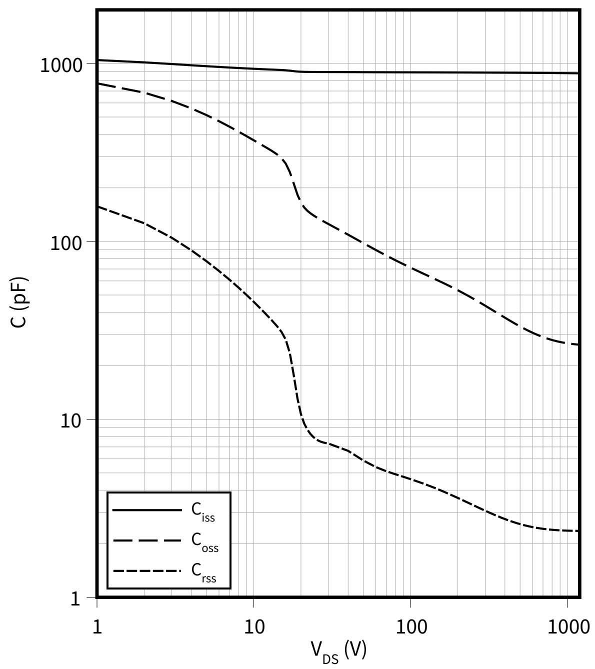
$I_D = 8.9$ A, $V_{DS} = 800$ V



Typical capacitance as a function of drain-source voltage

$C = f(V_{DS})$

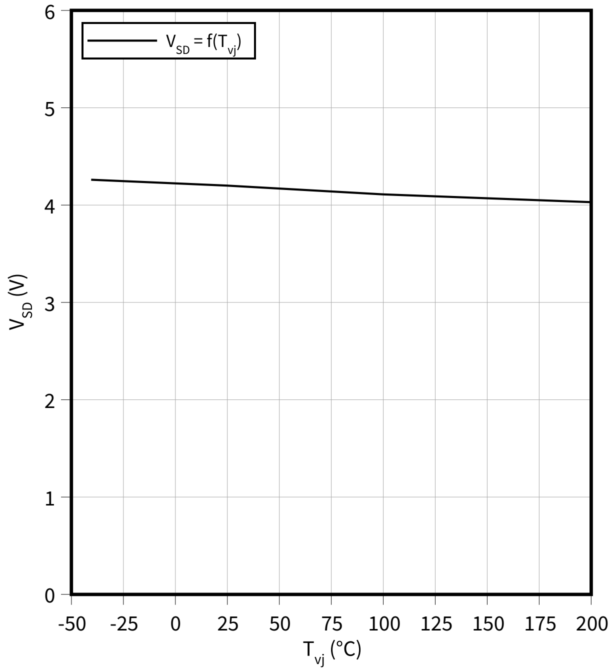
f = 100 kHz, $V_{GS} = 0$ V

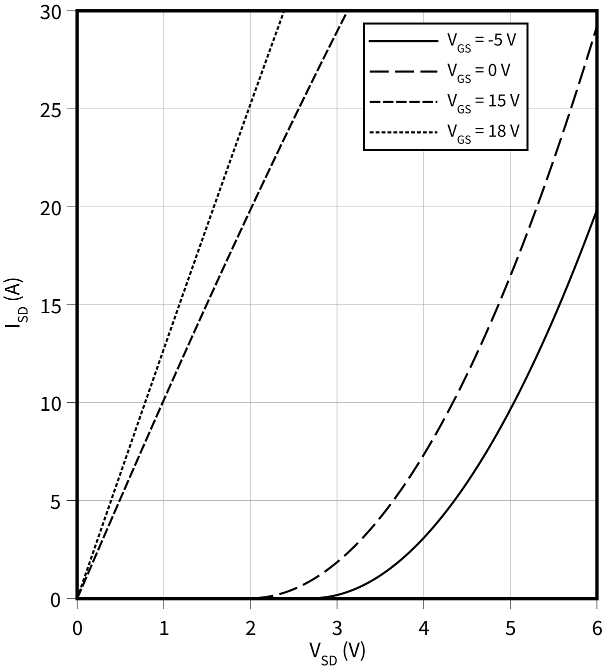
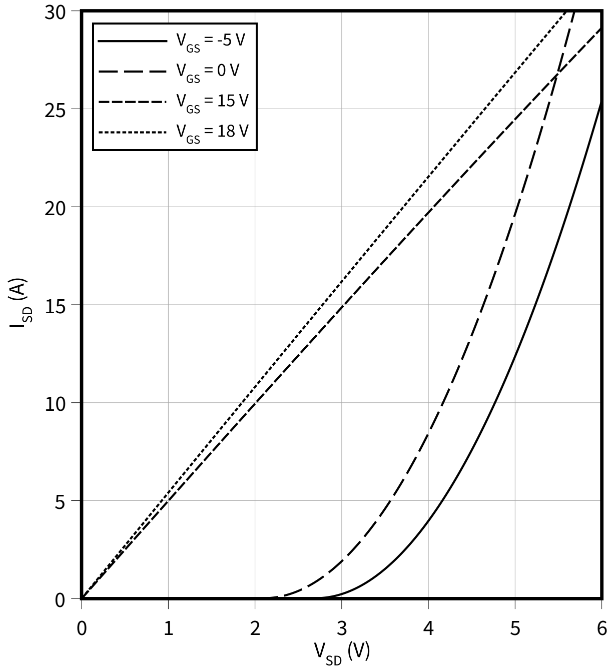
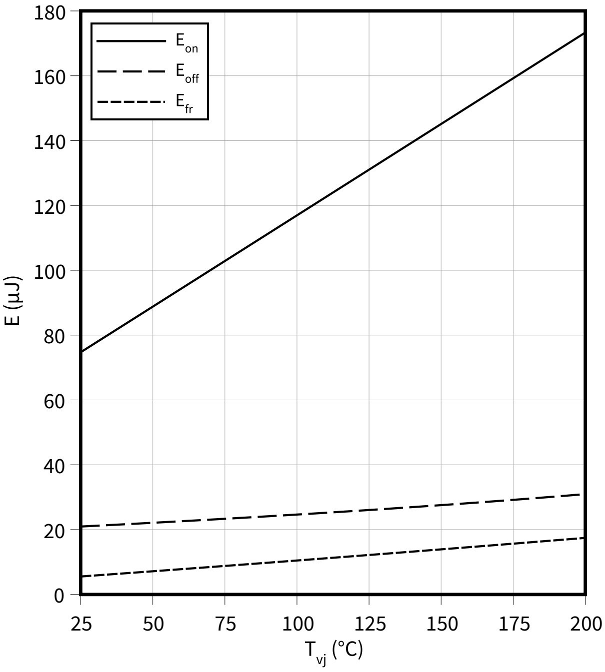
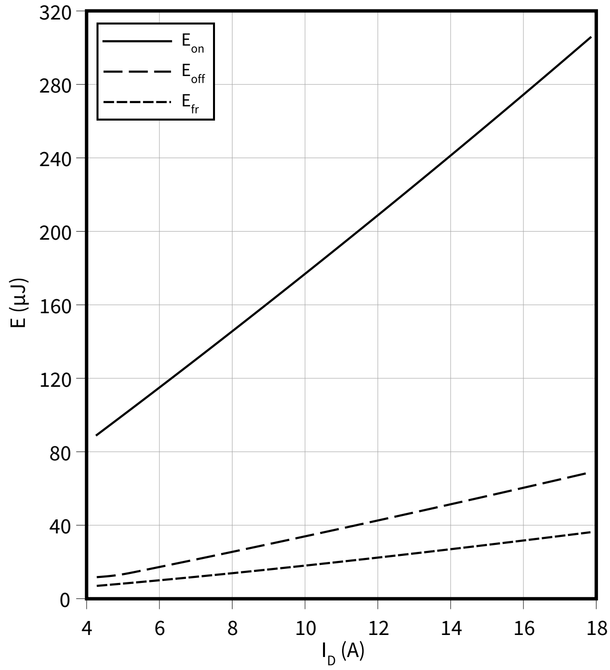


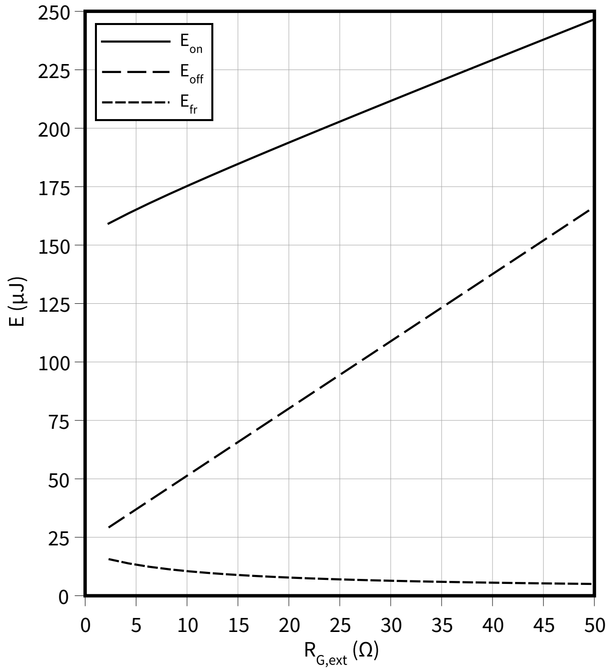
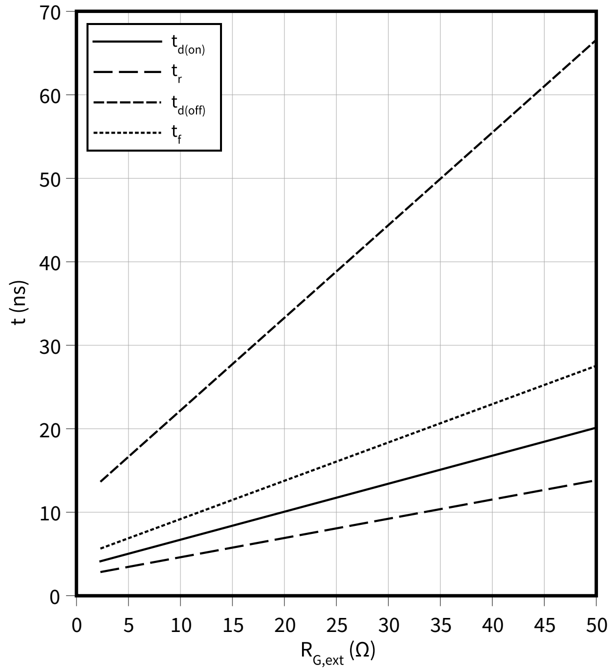
Typical reverse drain voltage as a function of junction temperature

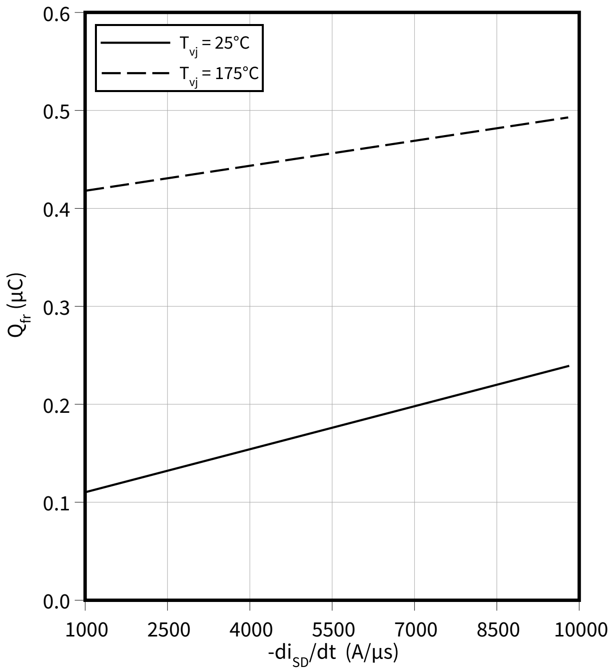
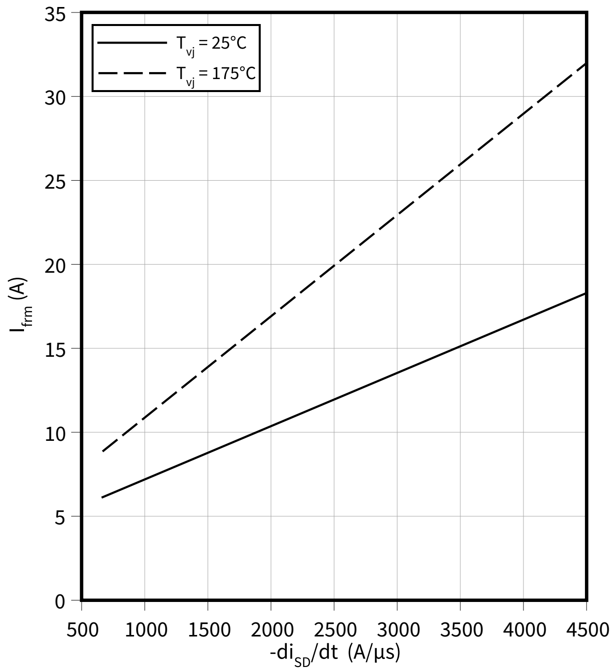
$V_{SD} = f(T_{vj})$

$I_{SD} = 8.9$ A, $V_{GS} = 0$ V

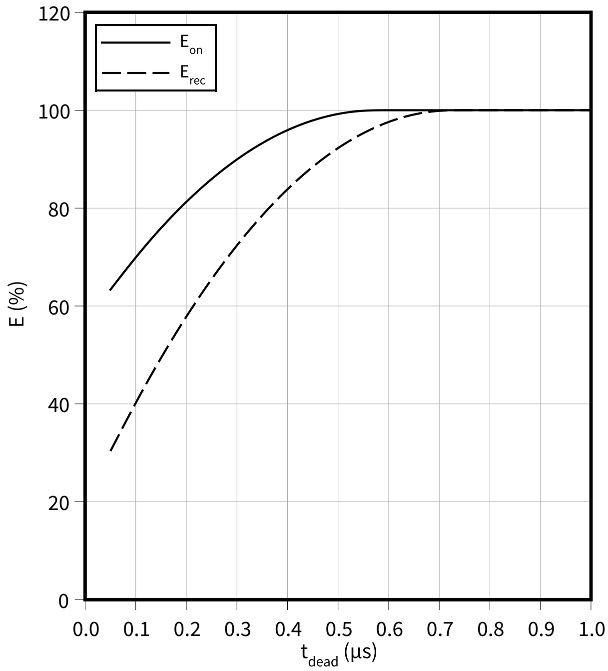


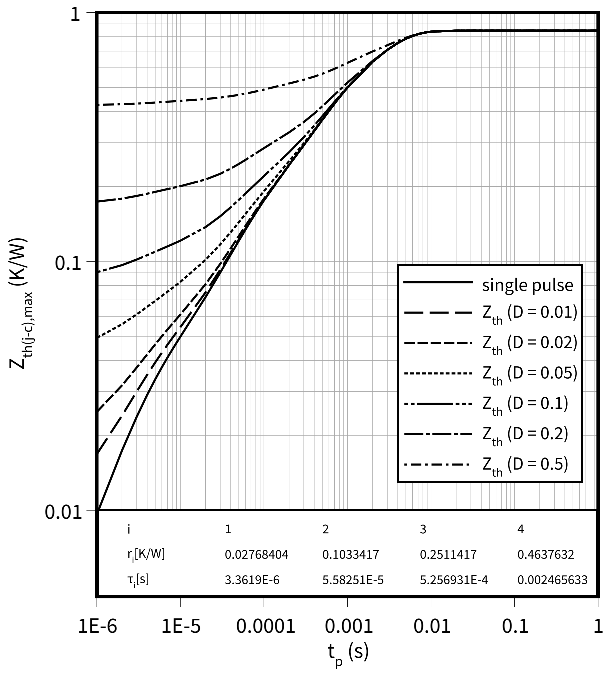
Typical reverse drain current as a function of reverse drain voltage, V_{GS} as a parameter $I_{SD} = f(V_{SD})$ $T_{vj} = 25\ °C$, $t_p = 20\ \mu s$	**Typical reverse drain current as a function of reverse drain voltage, V_{GS} as a parameter** $I_{SD} = f(V_{SD})$ $T_{vj} = 175\ °C$, $t_p = 20\ \mu s$
	
Typical switching energy as a function of junction temperature, test circuit in Fig. F, 2nd device own body diode: V_{GS} = 0 V $E = f(T_{vj})$ V_{GS} = 0/18 V, I_D = 8.9 A, $R_{G,ext}$ = 2.3 Ω, V_{DD} = 800 V	**Typical switching energy as a function of drain current, test circuit in Fig. F, 2nd device own body diode: V_{GS} = 0 V** $E = f(I_D)$ V_{GS} = 0/18 V, T_{vj} = 175 °C, $R_{G,ext}$ = 2.3 Ω, V_{DD} = 800 V
	

Typical switching energy as a function of gate resistance, test circuit in Fig. F, 2nd device own body diode: V_{GS} = 0 V	Typical switching times as a function of gate resistance, test circuit in Fig. F, 2nd device own body diode: V_{GS} = 0 V
$E = f(R_{G,ext})$	$t = f(R_{G,ext})$
V_{GS} = 0/18 V, I_D = 8.9 A, T_{vj} = 175 °C, V_{DD} = 800 V	V_{GS} = 0/18 V, I_D = 8.9 A, T_{vj} = 175 °C, V_{DD} = 800 V
	

Typical reverse recovery charge as a function of reverse drain current slope, test circuit in Fig. F, 2nd device own body diode: V_{GS} = 0 V	Typical reverse recovery current as a function of reverse drain current slope, test circuit in Fig. F, 2nd device own body diode: V_{GS} = 0 V
$Q_{fr} = f(-di_{SD}/dt)$	$I_{frm} = f(-di_{SD}/dt)$
V_{GS} = 0/18 V, I_{SD} = 8.9 A, V_{DD} = 800 V	V_{GS} = 0/18 V, I_{SD} = 8.9 A, V_{DD} = 800 V
	

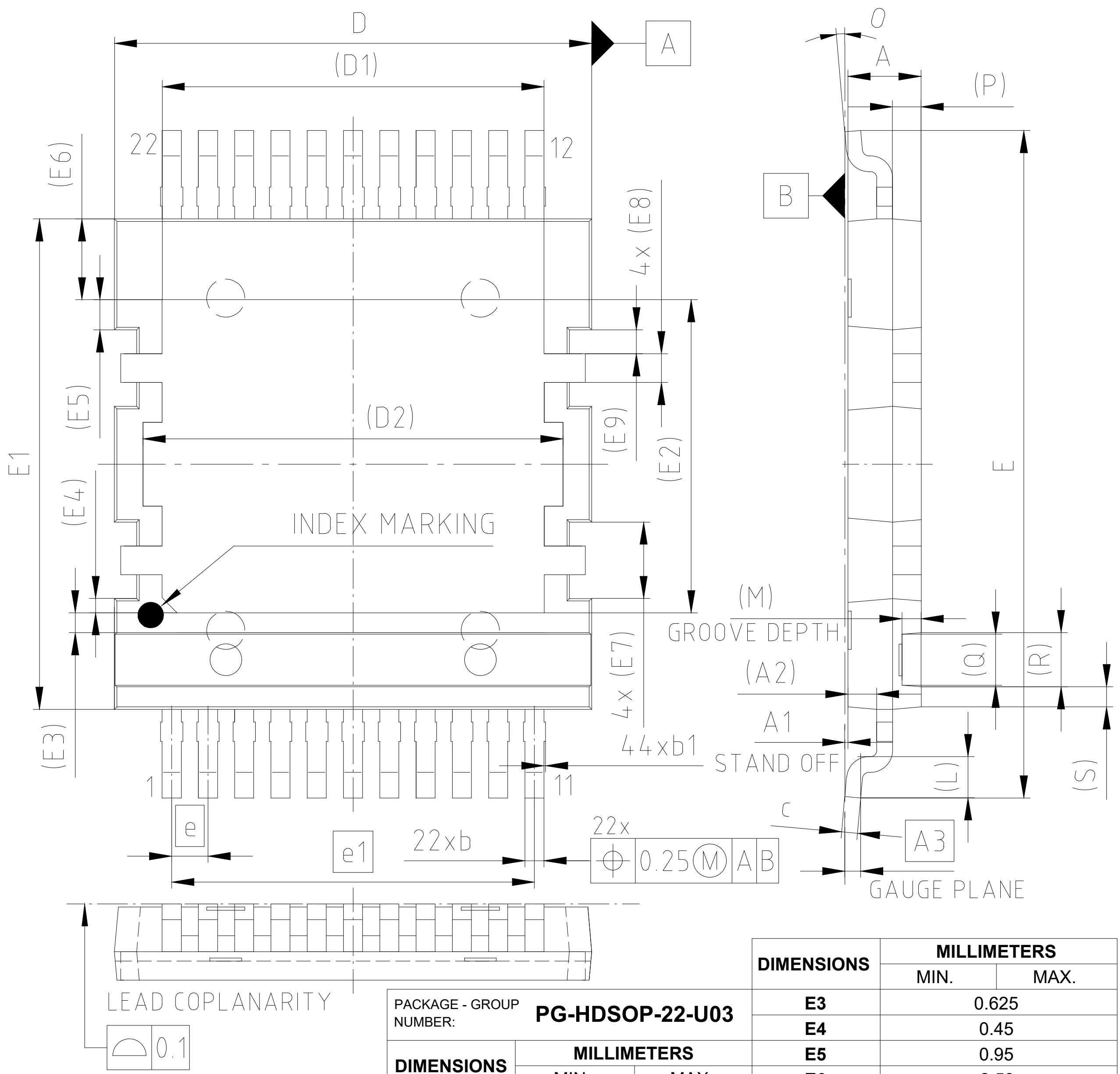
Typical switching energy as a function of dead time / blanking time, test circuit in Fig. F, 2nd device own body diode: V_{GS} = -5 V $E = f(t_{dead})$ T_{vj} = 175 °C, $R_{G,ext}$ = 2.3 Ω, V_{GS} = 0/18 V, I_D = 8.9 A V_{DD} = 800 V	**Max. transient thermal impedance (MOSFET/diode)** $Z_{th(j\text{-}c),max} = f(t_p)$ $D = t_p/T$





i	1	2	3	4
r_i[K/W]	0.02768404	0.1033417	0.2511417	0.4637632
τ_i[s]	3.3619E-6	5.58251E-5	5.256931E-4	0.002465633

5 Package outlines



NOTES:

ALL METAL SURFACES TIN PLATED EXCEPT AREA OF CUT

DIMENSIONS DO NOT INCLUDE MOLD FLASH, PROTRUSION OR GATE BURRS

PACKAGE - GROUP NUMBER:	PG-HDSOP-22-U03	
DIMENSIONS	**MILLIMETERS**	
	MIN.	MAX.
A	2.25	2.35
A1	0.00	0.15
A2	0.90	
A3	0.50	
b	0.50	0.70
b1	---	0.15
c	0.46	0.58
D	14.90	15.10
D1	12.00	
D2	13.20	
E	20.81	21.11
E1	15.30	15.50
E2	9.83	

DIMENSIONS	**MILLIMETERS**	
	MIN.	MAX.
E3	0.625	
E4	0.45	
E5	0.95	
E6	2.53	
E7	2.40	
E8	0.90	
E9	0.75	
e	1.14	
e1	11.4	
L	1.30	
M	0.60	
N	22	
O	0°	8°
P	0.90	
Q	1.60	
R	1.70	
S	0.631	

Figure 1

6 Testing conditions

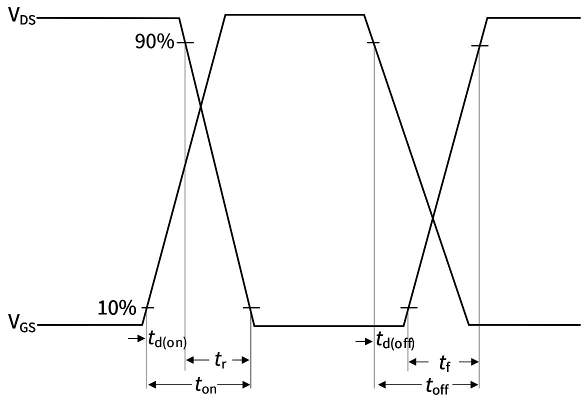


Figure A. **Definition of switching times**

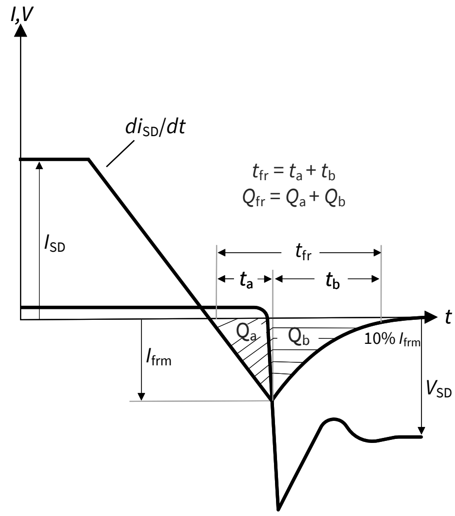


Figure B. **Definition of body diode switching characteristics**

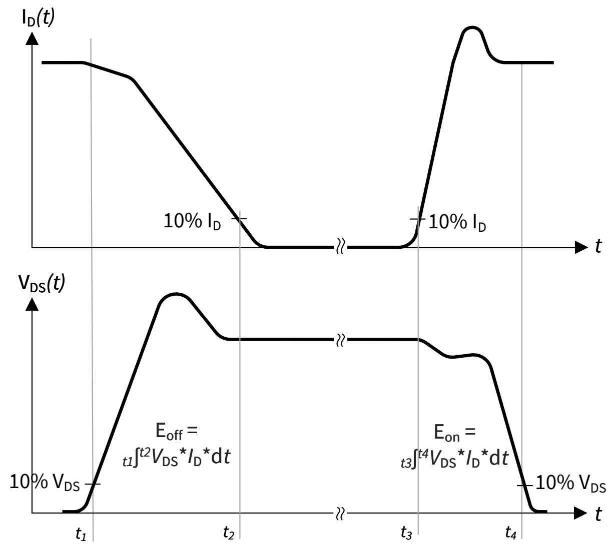


Figure C. **Definition of switching losses**

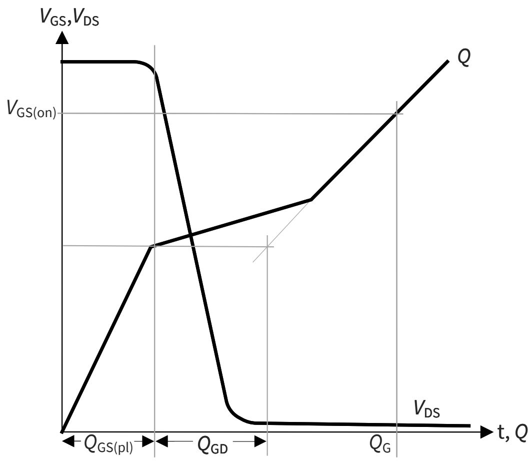


Figure D. **Definition of QGD**

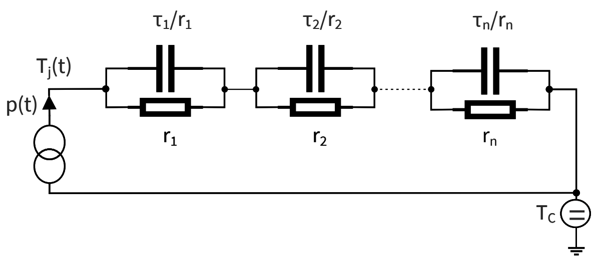


Figure E. **Thermal equivalent circuit**

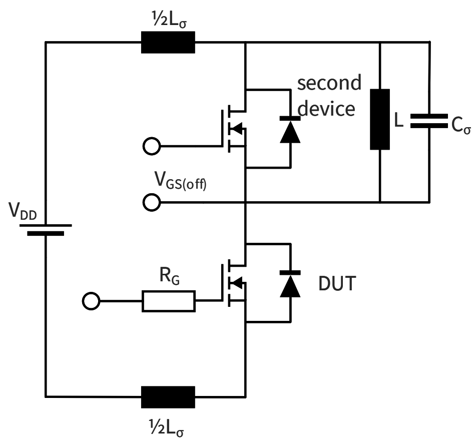


Figure F. **Dynamic test circuit**
Parasitic inductance L_σ,
Parasitic capacitor C_σ,

Figure 2

Revision history

Document revision	Date of release	Description of changes
0.10	2024-11-20	Preliminary datasheet
1.00	2024-12-12	Final datasheet

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